# MOSFET – Power, Dual N-Channel, Logic Level, Dual SO8FL

## 60 V, 33 mΩ, 22 A

# NTMFD5875NL

**ON Semiconductor®**

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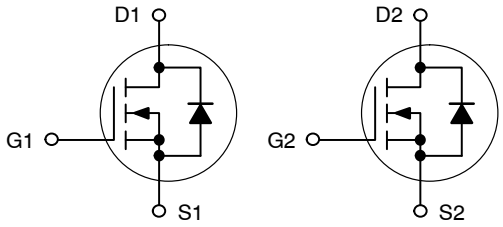
### Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- These Devices are Pb−Free, Halogen Free and are RoHS Compliant

| $V_{(BR)DSS}$ | $R_{DS(on)}$ MAX | $I_D$ MAX |
|---|---|---|
| 60 V | 33 mΩ @ 10 V | 22 A |
| | 45 mΩ @ 4.5 V | |

**Dual N−Channel**




### MAXIMUM RATINGS ($T_J$ = 25°C unless otherwise noted)

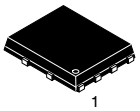
| Parameter | | | Symbol | Value | Unit |
|---|---|---|---|---|---|
| Drain−to−Source Voltage | | | $V_{DSS}$ | 60 | V |
| Gate−to−Source Voltage | | | $V_{GS}$ | ±20 | V |
| Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3, 4) | Steady State | $T_C$ = 25°C | $I_D$ | 22 | A |
| | | $T_C$ = 100°C | | 15 | |
| Power Dissipation $R_{\theta JC}$ (Notes 1, 2, 3) | | $T_C$ = 25°C | $P_D$ | 32 | W |
| | | $T_C$ = 100°C | | 16 | |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1 & 3, 4) | Steady State | $T_A$ = 25°C | $I_D$ | 7 | A |
| | | $T_A$ = 100°C | | 5.8 | |
| Power Dissipation $R_{\theta JA}$ (Notes 1, 3) | | $T_A$ = 25°C | $P_D$ | 3.2 | W |
| | | $T_A$ = 100°C | | 2.2 | |
| Pulsed Drain Current | $T_A$ = 25°C, $t_p$ = 10 μs | | $I_{DM}$ | 80 | A |
| Operating Junction and Storage Temperature | | | $T_J$, $T_{stg}$ | −55 to +175 | °C |
| Source Current (Body Diode) | | | $I_S$ | 19 | A |
| Single Pulse Drain−to−Source Avalanche Energy ($T_J$ = 25°C, $V_{DD}$ = 24 V, $V_{GS}$ = 10 V, $R_G$ = 25 Ω) | ($I_{L(pk)}$ = 14.5 A, L = 0.1 mH) | | $E_{AS}$ | 10.5 | mJ |
| | ($I_{L(pk)}$ = 6.3 A, L = 2 mH) | | | 40 | |
| Lead Temperature for Soldering Purposes (1/8″ from case for 10 s) | | | $T_L$ | 260 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

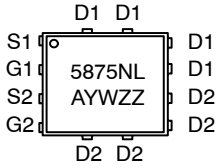
| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Junction−to−Case − Steady State (Note 2, 3) | $R_{\theta JC}$ | 4.65 | °C/W |
| Junction−to−Ambient − Steady State (Note 3) | $R_{\theta JA}$ | 47 | |

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51−12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface−mounted on FR4 board using a 650 $mm^2$, 2 oz. Cu pad.
4. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.




**DFN8 5x6 (SO8FL) CASE 506BT**

### MARKING DIAGRAM




5875NL = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

### ORDERING INFORMATION

| Device | Package | Shipping† |
|---|---|---|
| NTMFD5875NLT1G | DFN8 (Pb−Free) | 1500 / Tape & Reel |
| NTMFD5875NLT3G | DFN8 (Pb−Free) | 5000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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**ELECTRICAL CHARACTERISTICS** ($T_J$ = 25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| Drain−to−Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 μA | | 60 | | | V |
| Drain−to−Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | | | | 53 | | mV/°C |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 60 V | $T_J$ = 25°C | | | 1.0 | μA |
| | | | $T_J$ = 125°C | | | 10 | |
| Gate−to−Source Leakage Current | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ±20 V | | | | ±100 | nA |
| **ON CHARACTERISTICS** (Note 5) | | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS}$ = $V_{DS}$, $I_D$ = 250 μA | | 1.0 | | 3.0 | V |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | | | | 3.5 | | mV/°C |
| Drain−to−Source On Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10 V | $I_D$ = 7.5 A | | 27 | 33 | mΩ |
| | | $V_{GS}$ = 4.5 V | $I_D$ = 7.5 A | | 37 | 45 | |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$ = 15 V, $I_D$ = 5.0 A | | | 7.0 | | S |
| **CHARGES AND CAPACITANCES** | | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0 V, f = 1.0 MHz, $V_{DS}$ = 25 V | | | 540 | | pF |
| Output Capacitance | $C_{oss}$ | | | | 55 | | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | | 36 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS}$ = 4.5 V, $V_{DS}$ = 48 V, $I_D$ = 5.0 A | | | 5.9 | | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | | | 0.62 | | |
| Gate−to−Source Charge | $Q_{GS}$ | | | | 1.64 | | |
| Gate−to−Drain Charge | $Q_{GD}$ | | | | 2.80 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS}$ = 10 V, $V_{DS}$ = 48V, $I_D$ = 5.0A | | | 11 | 20 | nC |
| **SWITCHING CHARACTERISTICS** (Note 6) | | | | | | | |
| Turn−On Delay Time | $t_{d(on)}$ | $V_{GS}$ = 4.5 V, $V_{DS}$ = 48 V, $I_D$ = 5.0 A, $R_G$ = 2.5 Ω | | | 8.1 | | ns |
| Rise Time | $t_r$ | | | | 15.8 | | |
| Turn−Off Delay Time | $t_{d(off)}$ | | | | 11.8 | | |
| Fall Time | $t_f$ | | | | 3.9 | | |
| Turn−On Delay Time | $t_{d(on)}$ | $V_{GS}$ = 10 V, $V_{DS}$ = 48 V, $I_D$ = 5.0 A, $R_G$ = 2.5 Ω | | | 4.9 | | ns |
| Rise Time | $t_r$ | | | | 6.4 | | |
| Turn−Off Delay Time | $t_{d(off)}$ | | | | 14.5 | | |
| Fall Time | $t_f$ | | | | 2.4 | | |
| **DRAIN−SOURCE DIODE CHARACTERISTICS** | | | | | | | |
| Forward Diode Voltage | $V_{SD}$ | $V_{GS}$ = 0 V, $I_S$ = 5.0 A | $T_J$ = 25°C | | 0.8 | 1.2 | V |
| | | | $T_J$ = 125°C | | 0.7 | | |
| Reverse Recovery Time | $t_{RR}$ | $V_{GS}$ = 0 V, $d_{IS}/d_t$ = 100 A/μs, $I_S$ = 5.0 A | | | 14.5 | | ns |
| Charge Time | $t_a$ | | | | 11.5 | | |
| Discharge Time | $t_b$ | | | | 3.1 | | |
| Reverse Recovery Charge | $Q_{RR}$ | | | | 11 | | nC |
| **PACKAGE PARASITIC VALUES** | | | | | | | |
| Source Inductance | $L_S$ | $T_A$ = 25°C | | | 0.93 | | nH |
| Drain Inductance | $L_D$ | | | | 0.005 | | |
| Gate Inductance | $L_G$ | | | | 1.84 | | |
| Gate Resistance | $R_G$ | | | | 1.5 | | Ω |

5. Pulse Test: pulse width = 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

## TYPICAL CHARACTERISTICS

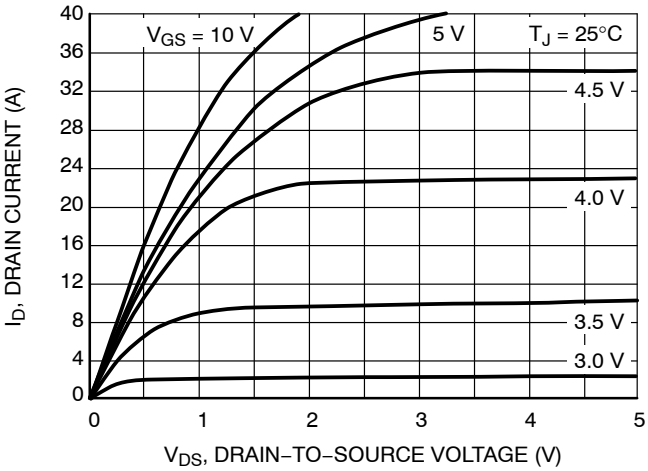



**Figure 1. On−Region Characteristics**

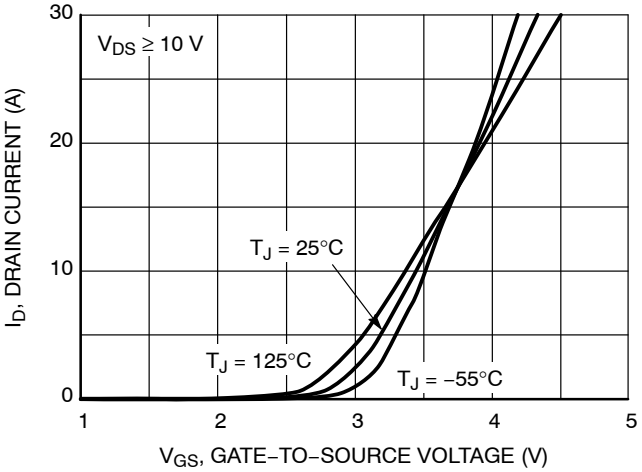



**Figure 2. Transfer Characteristics**

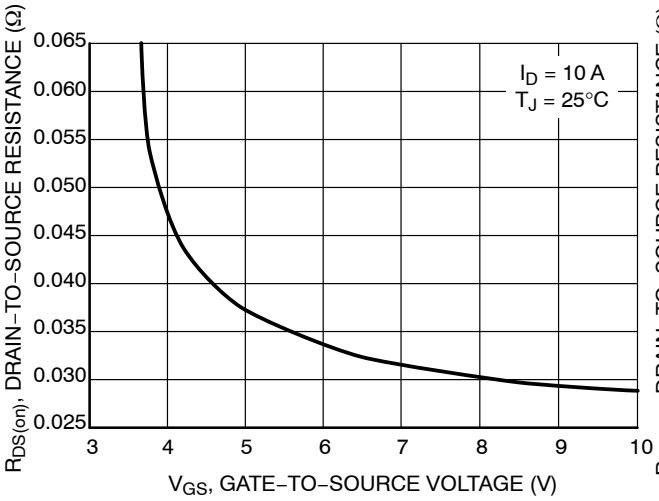



**Figure 3. On−Resistance vs. Gate−to−Source Voltage**

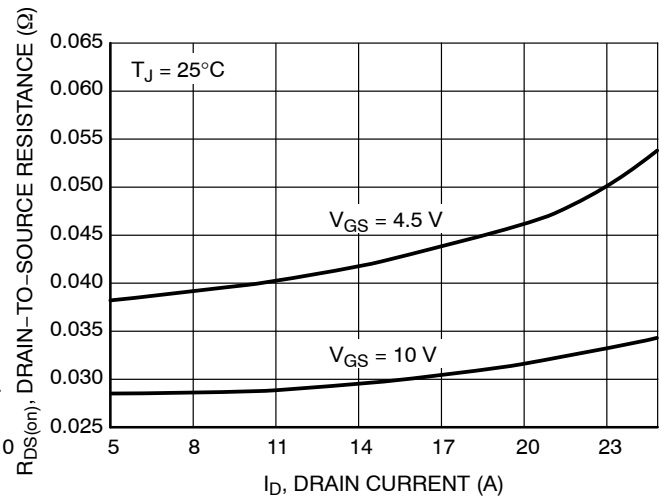



**Figure 4. On−Resistance vs. Drain Current and Gate Voltage**

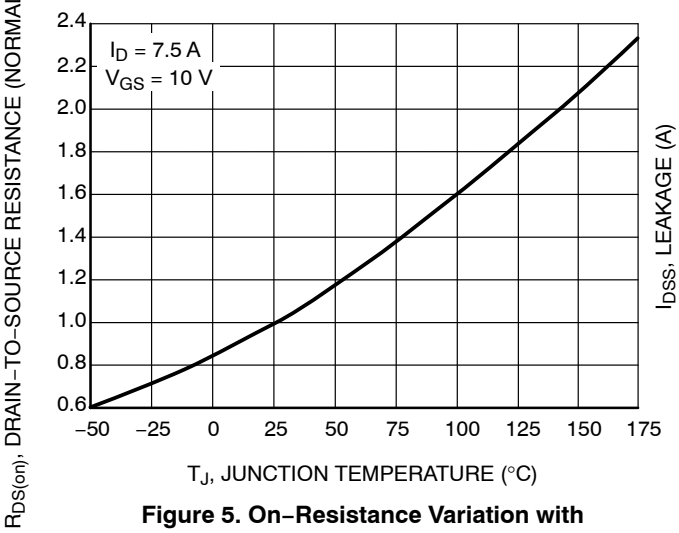



**Figure 5. On−Resistance Variation with Temperature**

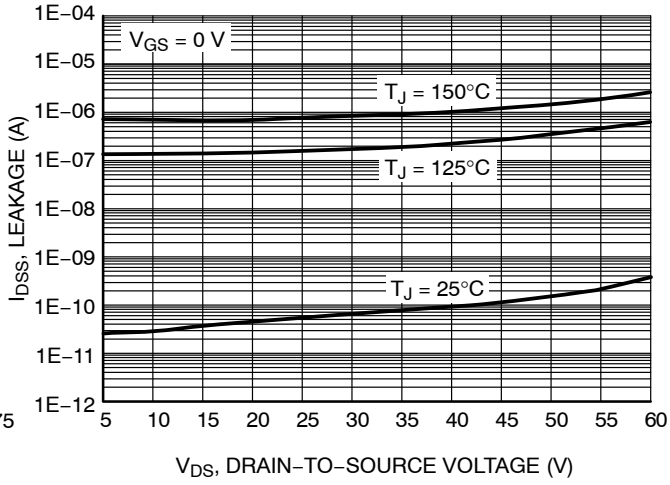



**Figure 6. Drain−to−Source Leakage Current vs. Voltage**

## TYPICAL CHARACTERISTICS

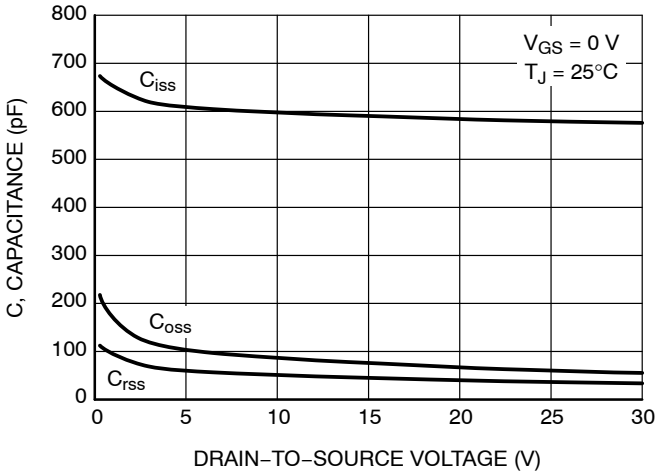



**Figure 7. Capacitance Variation**

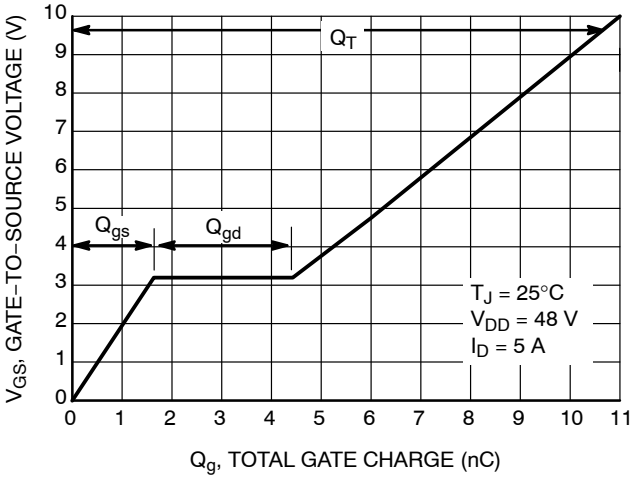



**Figure 8. Gate−to−Source vs. Gate Charge**

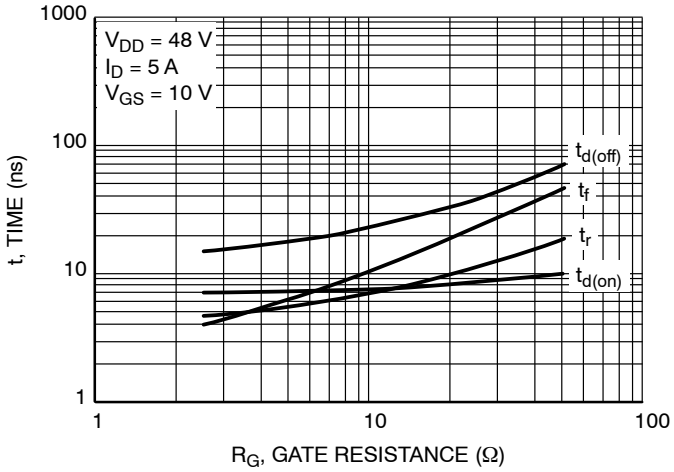



**Figure 9. Resistive Switching Time Variation vs. Gate Resistance**

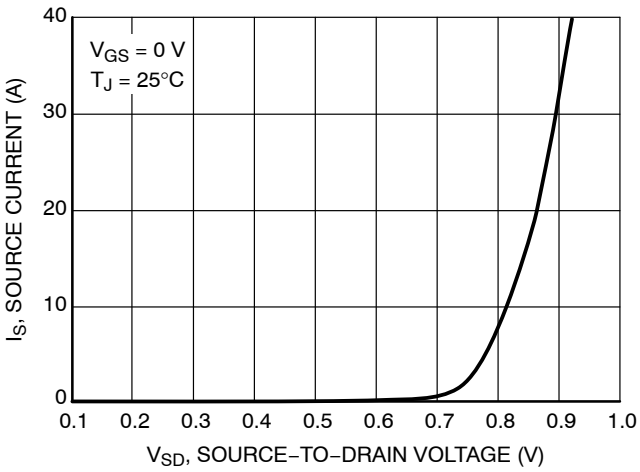



**Figure 10. Diode Forward Voltage**

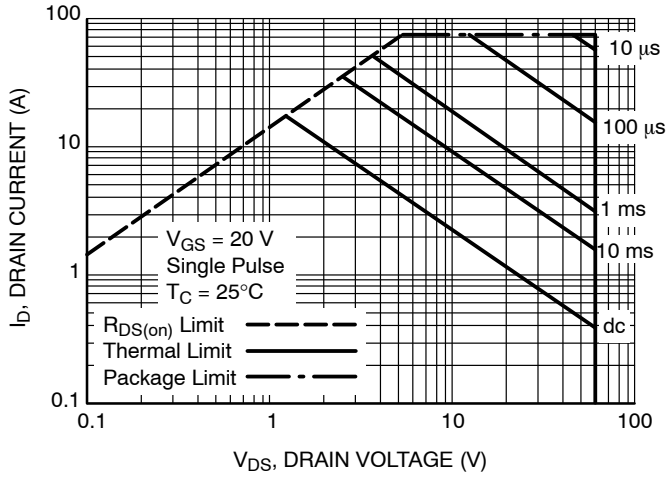



**Figure 11. Maximum Rated Forward Biased Safe Operating Area**

## TYPICAL CHARACTERISTICS

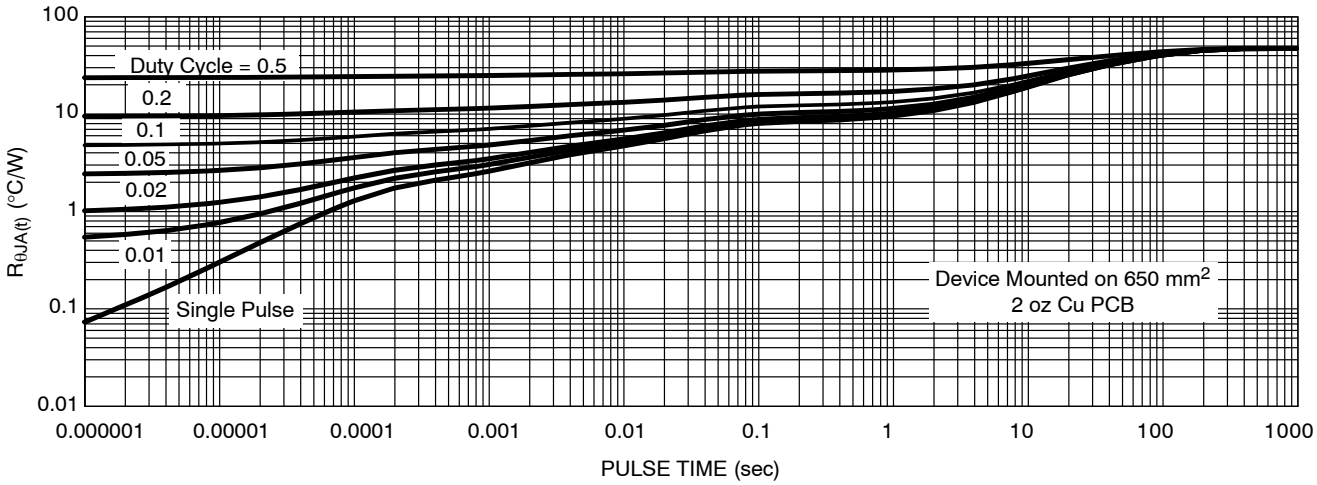
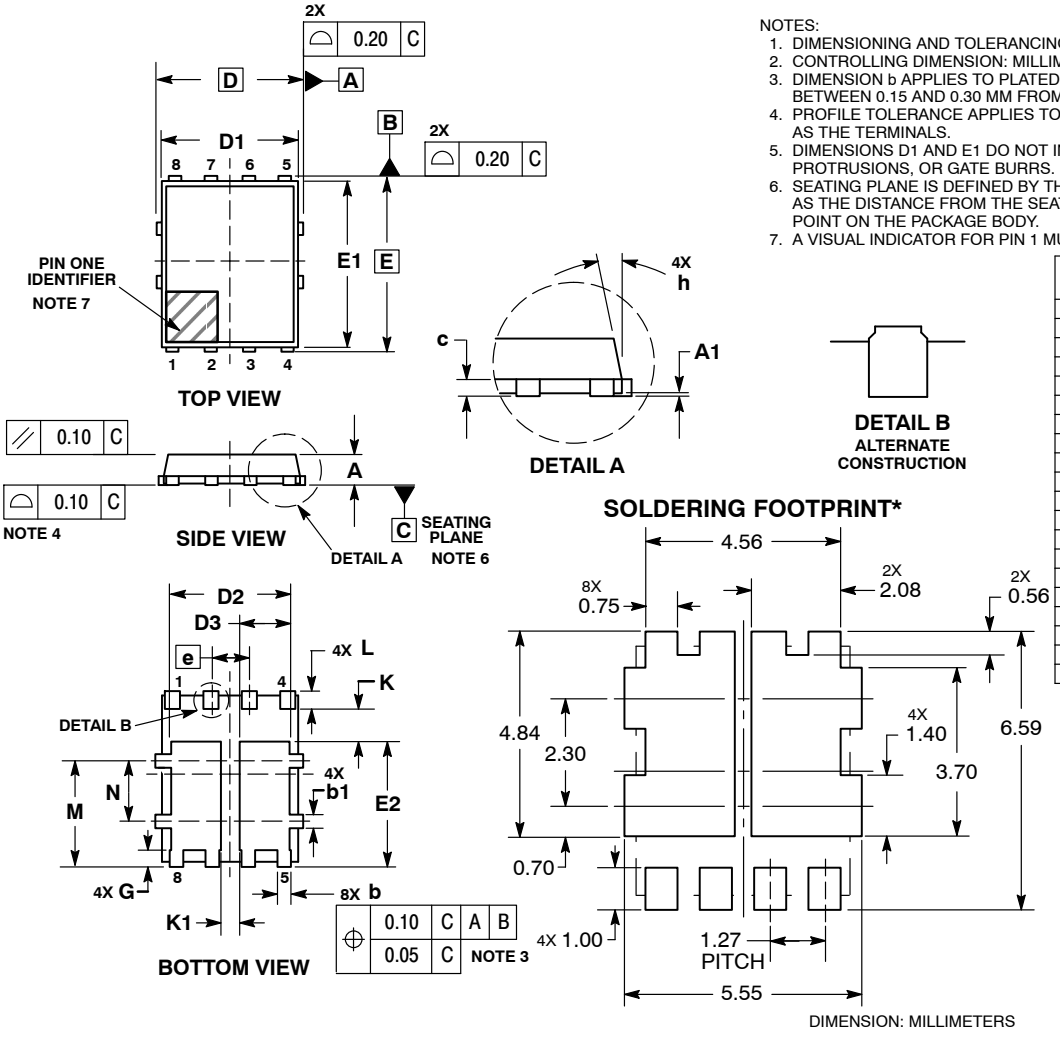



**Figure 12. Thermal Response**

## PACKAGE DIMENSIONS

**DFN8 5x6, 1.27P Dual Flag (SO8FL−Dual)**
CASE 506BT
ISSUE E




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
4. PROFILE TOLERANCE APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
6. SEATING PLANE IS DEFINED BY THE TERMINALS. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
7. A VISUAL INDICATOR FOR PIN 1 MUST BE LOCATED IN THIS AREA.

| | MILLIMETERS | | |
|---|---|---|---|
| DIM | MIN | MAX | MAX |
| A | 0.90 | --- | 1.10 |
| A1 | --- | --- | 0.05 |
| b | 0.33 | 0.42 | 0.51 |
| b1 | 0.33 | 0.42 | 0.51 |
| c | 0.20 | --- | 0.33 |
| D | 5.15 BSC | | |
| D1 | 4.70 | 4.90 | 5.10 |
| D2 | 3.90 | 4.10 | 4.30 |
| D3 | 1.50 | 1.70 | 1.90 |
| E | 6.15 BSC | | |
| E1 | 5.70 | 5.90 | 6.10 |
| E2 | 3.90 | 4.15 | 4.40 |
| e | 1.27 BSC | | |
| G | 0.45 | 0.55 | 0.65 |
| h | --- | --- | 12 ° |
| K | 0.51 | --- | --- |
| K1 | 0.56 | --- | --- |
| L | 0.48 | 0.61 | 0.71 |
| M | 3.25 | 3.50 | 3.75 |
| N | 1.80 | 2.00 | 2.20 |

DIMENSION: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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